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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
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TAIWAN SEMICONDUCTOR

TSM4425

30V P-Channel MOSFET

Pb-Free RoHS COMPLIANT

SOP-8

Pin Definition:

1. Source 8. Drain
2. Source 7. Drain
3. Source 6. Drain
4. Gate 5. Drain

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$(mΩ)	I_D (A)
-30	14 @ V_{GS} = -10V	-11
	20 @ V_{GS} = -4.5V	-8.5

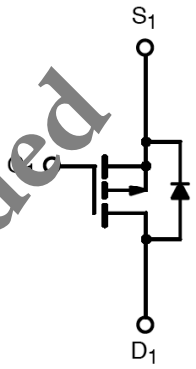
Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

- Load Switches
- Notebook PCs
- Desktop PCs

Block Diagram



P-Channel MOSFET

Ordering Information

Part No.	Package	Packing
TSM4425CS RLG	SOP-8	2.5Kpcs / 13" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Absolute Maximum Rating (T_C = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current		I_D	-11	A
Pulsed Drain Current		I_{DM}	-50	A
Continuous Source Current (Diode Conduction)[a,b]		I_S	-2.1	A
Maximum Power Dissipation	Ta = 25°C	P_D	2.5	W
	Ta = 75°C		1.6	
Operating Junction Temperature		T_J	+150	°C
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Foot Thermal Resistance	$R_{\Theta JF}$	18	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R_{\Theta JA}$	52.5	°C/W

Notes:

a. Pulse width limited by the Maximum junction temperature

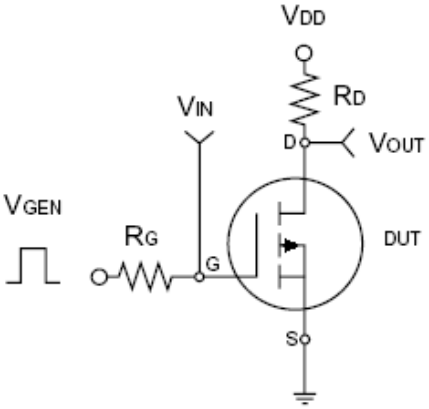
b. Surface Mounted on FR4 Board, t ≤ 10 sec.

TSM4425
30V P-Channel MOSFET

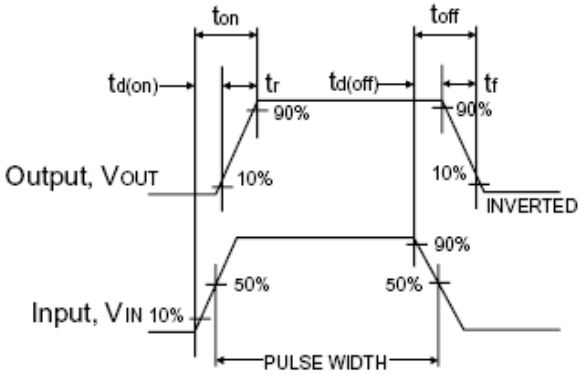
Electrical Specifications (T_C = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = -250uA	BV_{DSS}	-30	--	--	V
Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250μA	$V_{GS(TH)}$	-1	--	-3	V
Gate Body Leakage	V_{GS} = ±20V, V_{DS} = 0V	I_{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V_{DS} = -30V, V_{GS} = 0V	I_{DSS}	--	--	-1.0	μA
On-State Drain Current[a]	V_{DS} = -5V, V_{GS} = -10V	$I_{D(ON)}$	-50	--	--	A
Drain-Source On-State Resistance[a]	V_{GS} = -10V, I_D = -11A	$R_{DS(ON)}$	--	10	12	mΩ
	V_{GS} = -4.5V, I_D = -8.5A		--	15	19	
Forward Transconductance[a]	V_{DS} = -15V, I_D = -11A	g_{fs}	--	23	--	S
Diode Forward Voltage	I_S = -2.1A, V_{GS} = 0V	V_{SD}	--	--	-1.3	V
Dynamic[b]						
Total Gate Charge	V_{DS} = -15V, I_D = -11A, V_{GS} = -10V	Q_g	--	64	--	nC
Gate-Source Charge		Q_{gs}	--	11	--	
Gate-Drain Charge		Q_{gd}	--	25	--	
Input Capacitance	V_{DS} = -8V, V_{GS} = 0V, f = 1.0MHz	C_{iss}	--	3680	--	pF
Output Capacitance		C_{oss}	--	930	--	
Reverse Transfer Capacitance		C_{rss}	--	620	--	
Switching[c]						
Turn-On Delay Time	V_{DD} = -15V, R_L = 15Ω, I_D = -1A, V_{GEN} = -10V, R_G = 6Ω	$t_{d(on)}$	--	15	--	ns
Turn-On Rise Time		t_r	--	13	--	
Turn-Off Delay Time		$t_{d(off)}$	--	100	--	
Turn-Off Fall Time		t_f	--	53	--	

Notes:
a. pulse test: PW ≤ 300μs, duty cycle ≤ 2%
b. For DESIGN AID ONLY, not subject to production testing.
b. Switching time is essentially independent of operating temperature.



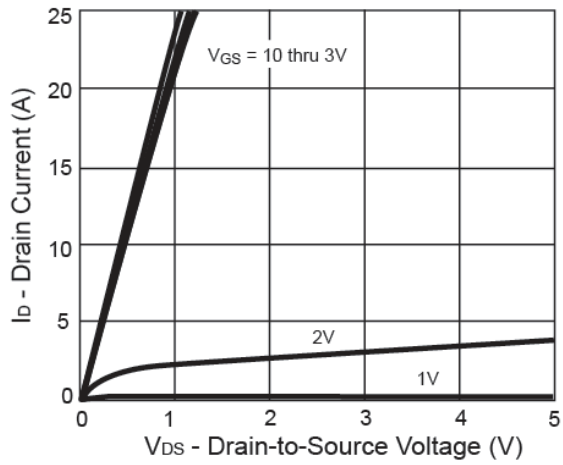
Switching Test Circuit



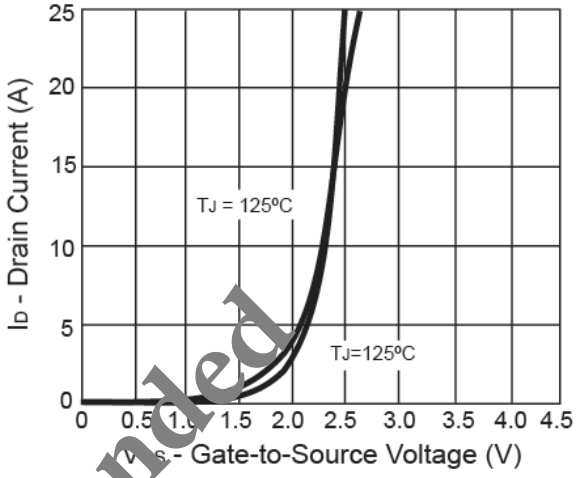
Switchin Waveforms

Electrical Characteristics Curve

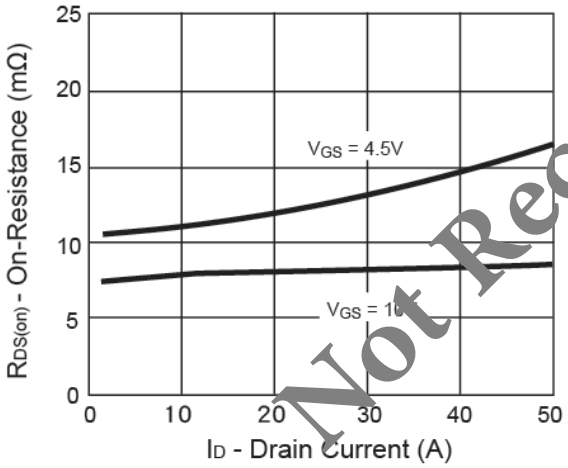
Output Characteristics



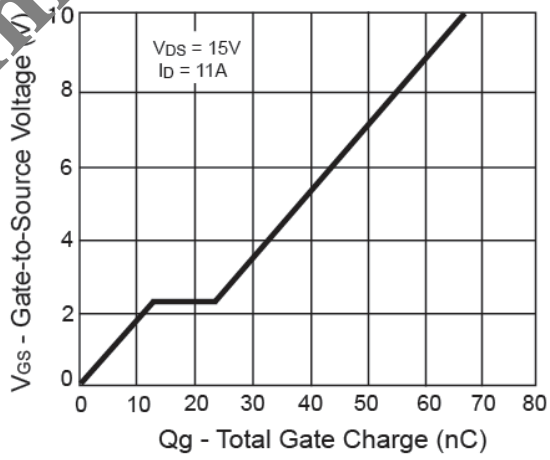
Transfer Characteristics



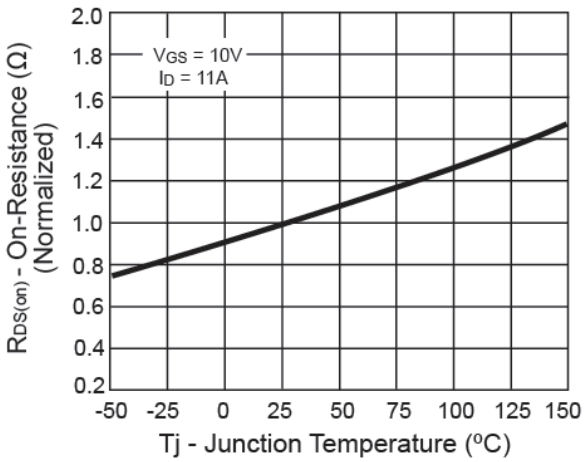
On-Resistance vs. Drain Current



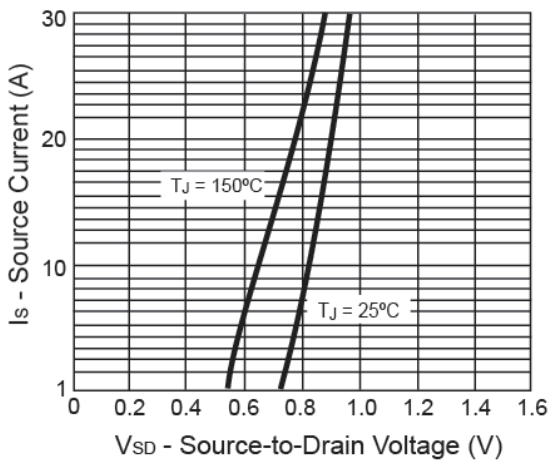
Gate Charge



On-Resistance vs. Junction Temperature

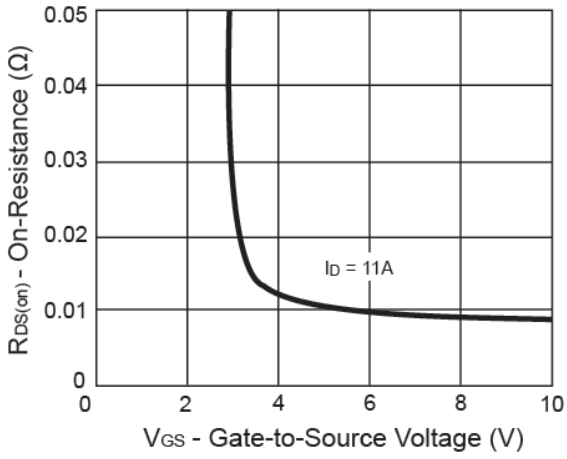


Source-Drain Diode Forward Voltage

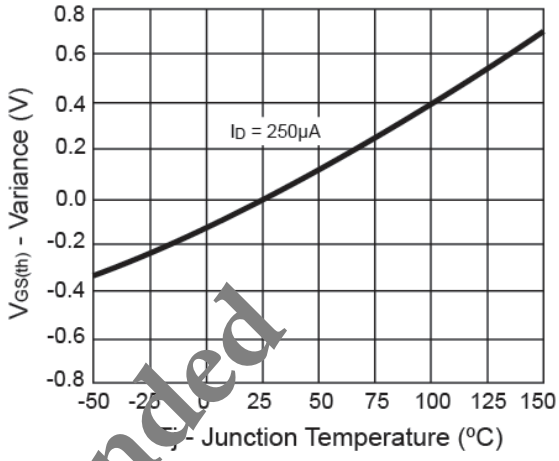


Electrical Characteristics Curve

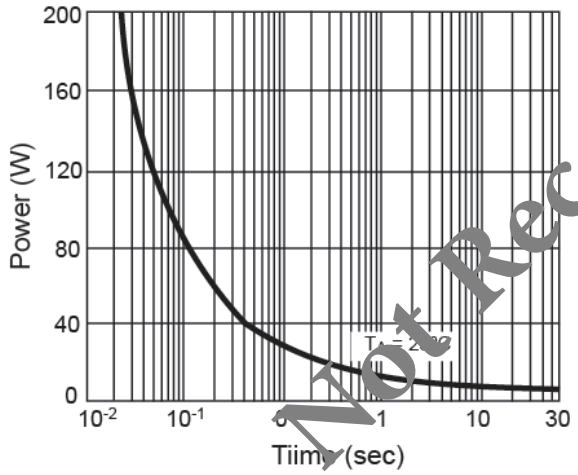
On-Resistance vs. Gate-Source Voltage



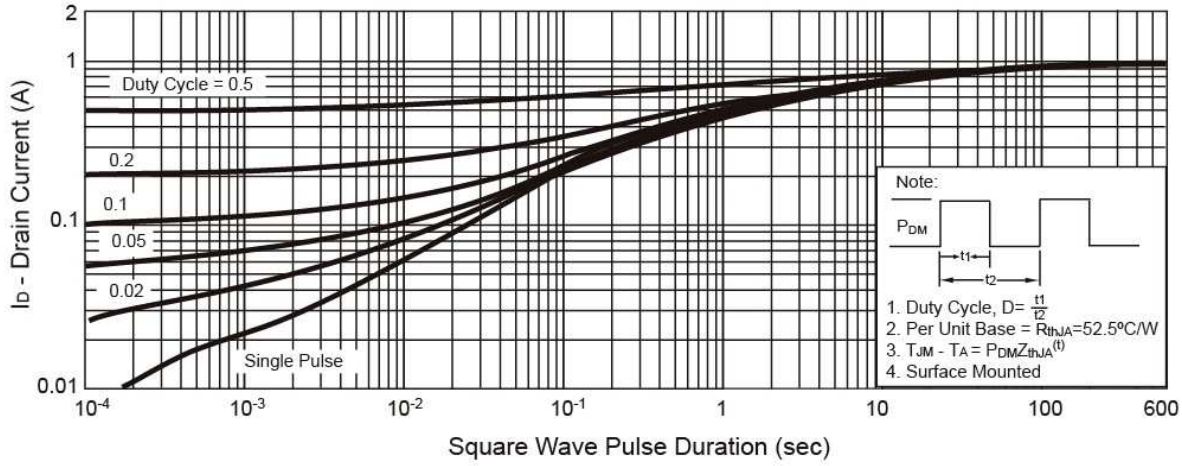
Threshold Voltage



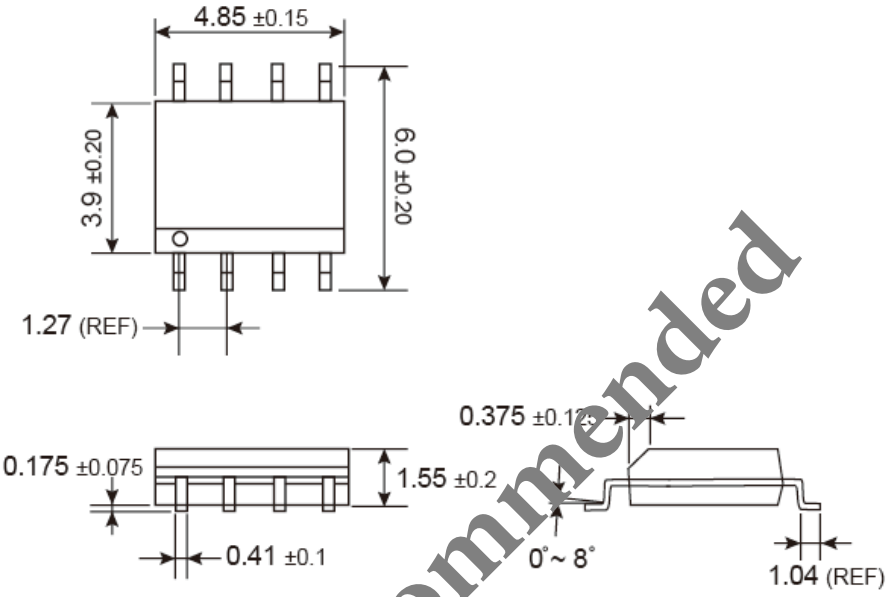
Single Pulse Power



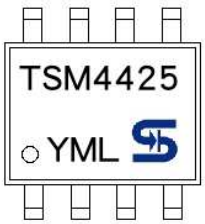
Normalized Thermal Transient Impedance, Junction-to-Ambient



SOP-8 Mechanical Drawing



Marking Diagram



Y = Year Code
M = Month Code for Halogen Free Product

O =Jan	**P** =Feb	**Q** =Mar	**R** =Apr
S =May	**T** =Jun	**U** =Jul	**V** =Aug
W =Sep	**X** =Oct	**Y** =Nov	**Z** =Dec

L = Lot Code

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